

GaAs IC SPDT Switch

Non-Reflective DC–10 GHz



AS018M2-01, AS018M2-10

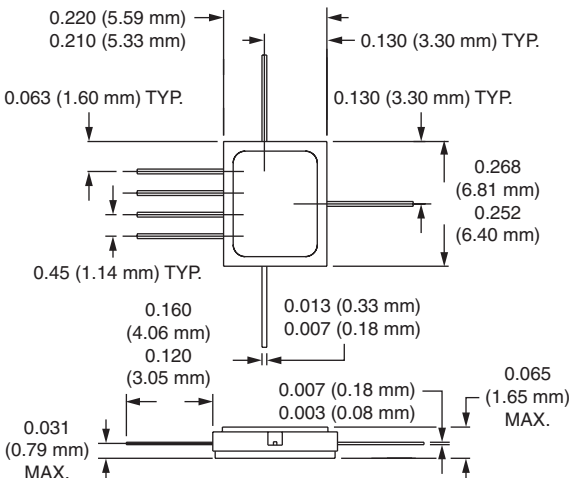
Features

- Broadband DC–10 GHz
- High Isolation, Non-Reflective
- 7 Lead Hermetic Package
- Capable of Meeting MIL-STD Requirements⁵

Description

The AS018M2-01 is a GaAs IC FET SPDT non-reflective switch. This device is ideal for microstrip applications and has optimum performance at higher frequencies (4–10 GHz), since all leads are RF isolated. This product is useful as a modulator and switch in high reliability and commercial applications. The AS018M2-10 is the gullwing version of this device for surface mount applications.

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Electrical Specifications at 25°C

Parameter ¹	Frequency ⁴	Min.	Typ.	Max.	Unit
Insertion Loss ²	DC–2.0 GHz		1.3	1.5	dB
	DC–4.0 GHz		1.6	1.8	dB
	DC–8.0 GHz		2.5	2.8	dB
	DC–10.0 GHz		3.2	3.5	dB
Isolation	DC–2.0 GHz	55	60		dB
	DC–4.0 GHz	50	55		dB
	DC–8.0 GHz	40	45		dB
	DC–10.0 GHz	30	35		dB
VSWR (I/O)	DC–2.0 GHz		1.2:1	1.4:1	
	DC–4.0 GHz		1.3:1	1.5:1	
	DC–8.0 GHz		1.6:1	1.8:1	
	DC–10.0 GHz		1.8:1	2.0:1	

Operating Characteristics at 25°C

Parameter	Condition	Frequency	Min.	Typ.	Max.	Unit
Switching Characteristics	Rise, Fall (10/90% or 90/10% RF)				1	μS
	On, Off (50% CTL to 90/10% RF)				1	μS
Input Power for 1 dB Compression	0/-5 V	0.5–10 GHz		24		dBm
		0.001 GHz		16		dBm
Intermodulation Intercept Point (IP3)	For Two-tone Input Power 13 dBm	0.5–10 GHz		46		dBm
		0.001 GHz		35		dBm
Control Voltages	$V_{Low} = 0 \text{ to } -0.2 \text{ V @ } 20 \mu\text{A Max.}$ $V_{High} = -3 \text{ V to } -6 \text{ V @ } 200 \mu\text{A Max.}$					

1. All measurements made in a 50 Ω system, unless otherwise specified.

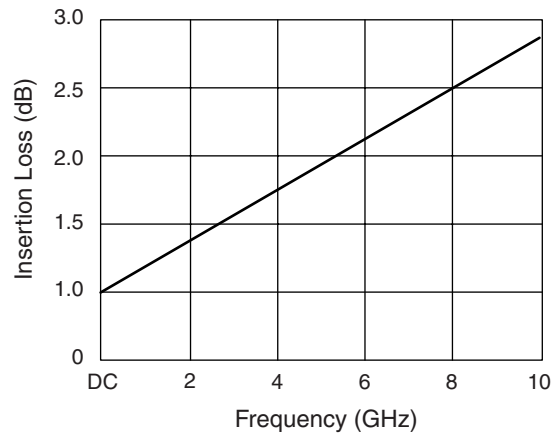
2. Insertion loss changes by 0.003 dB/°C.

3. Video feedthru measured with 1 ns risetime pulse and 500 MHz bandwidth.

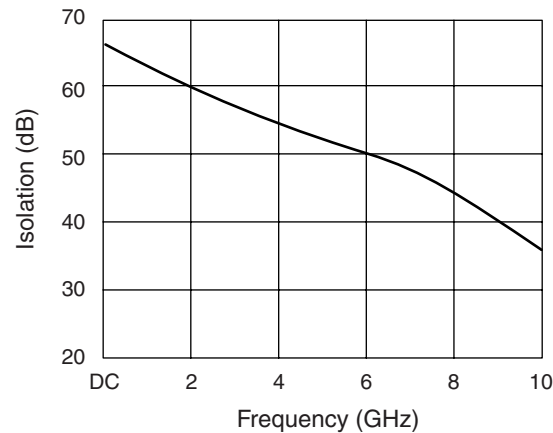
4. DC = 300 kHz.

5. See Quality/Reliability section.

Typical Performance Data



Insertion Loss vs. Frequency

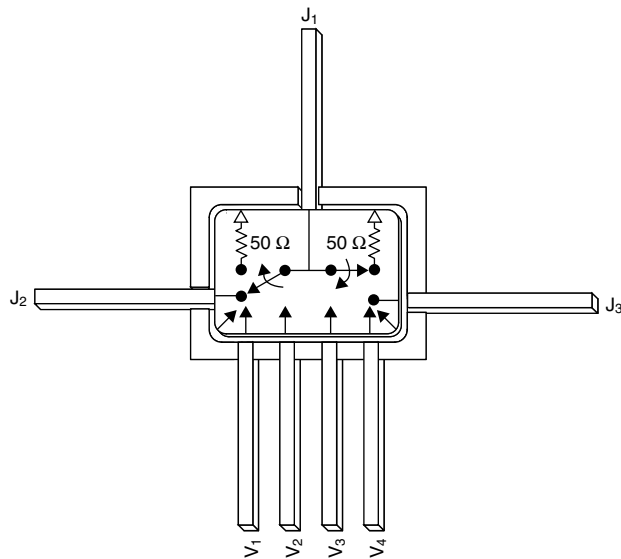


Isolation vs. Frequency

Truth Table

V ₁	V ₂	V ₃	V ₄	J ₁ –J ₂	J ₁ –J ₃
0	-5	0	-5	Insertion Loss	Isolation
-5	0	-5	0	Isolation	Insertion Loss

Pin Out



Absolute Maximum Ratings

Characteristic	Value
RF Input Power (RF In)	1 W
Control Voltage (V _C)	+0.2 V, -7.0 V
Operating Temperature (T _{OP})	-55°C to +125°C
Storage Temperature (T _{ST})	-65°C to +150°C
Thermal Resistance (Θ _{JC})	83°C/W

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